



40V Dual N-Channel Enhancement Mode MOSFET

Voltage

40 V

Current

35 A

Features

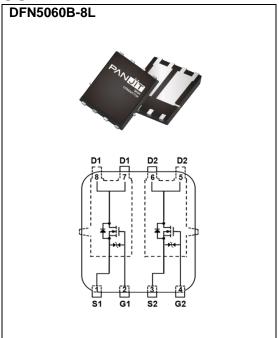
- RDS(ON), VGS@10V, ID@10A<13.4 $m\Omega$
- RDS(ON), VGS@7V, ID@6A<17m Ω
- Excellent FOM
- Standard Level Drive
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: DFN5060B-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.092 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	40	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current(Note 3)	T _C =25°C	l _D	35	А	
	T _C =100°C		25		
Pulsed Drain Current(Note 1)	T _C =25°C	I _{DM}	140		
Power Dissipation	T _C =25°C	D-	32	W	
	T _C =100°C	Po	16		
Continuous Drain Current(Note 4)	T _A =25°C	I _D	10.5	^	
	T _A =70°C		8.8	Α	
Power Dissipation	T _A =25°C	D-	2.4	W	
	T _A =70°C	Po	1.7		
Single Pulse Avalanche Energy ^(Note 5)		Eas	42	mJ	
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~175	°C	
Thermal Resistance ^(Note 4)	Junction to Case	$R_{ heta JC}$	5	°C/W	
	Junction to Ambient	$R_{\theta JA}$	60		





Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	40	-	-	V	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =50uA	2	2.8	3.5		
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =10A	-	10.7	13.4	mΩ	
		V _{GS} =7V, I _D =6A	-	13	17		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V	-	-	1	uA	
<u>-</u>		V _{GS} =±20V, V _{DS} =0V	-	-	±10	uA	
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±10V, V _{DS} =0V	-	-	±1		
Dynamic ^(Note 6)							
Total Gate Charge	Q_g	\/ 20\/ L 40A	-	9.5	-	nC	
Gate-Source Charge	Qgs	V _{DS} =32V, I _D =10A,	-	4.2	-		
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	2.6	-		
Input Capacitance	Ciss)/ OE)/)/ O)/	-	673	-		
Output Capacitance	Coss	V _{DS} =25V, V _{GS} =0V,	-	176	-	pF	
Reverse Transfer Capacitance	Crss	f=1MHz	-	29	-		
Gate resistance	Rg	f=1MHz	-	1.4	-	Ω	
Turn-On Delay Time	td _(on)	.,	-	10	-		
Turn-On Rise Time	tr	V _{DS} =32V, I _D =10A,	-	3	-	ns	
Turn-Off Delay Time	td _(off)	$V_{GS}=10V, R_{G}=3\Omega$	-	18	-		
Turn-Off Fall Time	tf	(Note 2)	-	3	-		
Drain-Source Diode				•		•	
Diode Forward Current	Is	Tc=25°C	-	-	35	_	
Pulsed Diode Forward Current	I _{SM}	1c=25 C	-	-	140	Α	
Diode Forward Voltage	V _{SD}	Is=20A, V _G s=0V	-	0.9	1.3	V	
Reverse Recovery Time	Trr	V _{GS} =0V, I _S =20A	-	17	-	ns	
Reverse Recovery Charge	Qrr	dl _s /dt=100A/us	-	9	-	nC	

NOTES:

- 1. Pulse width<a>100us, Duty cycle<a>2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Chip capability with an R_{0JC}=5°C/W.
- 4. R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 5. The test condition is L=0.5mH, I_{AS} =13A, V_{DD} =30V, V_{GS} =10V, Starting T_{J} =25°C.
- 6. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

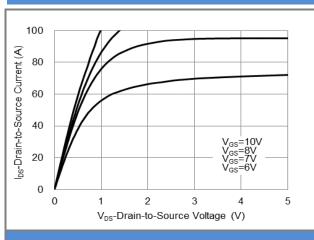


Fig.1 On-Region Characteristics

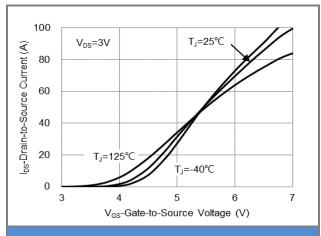


Fig.2 Transfer Characteristics

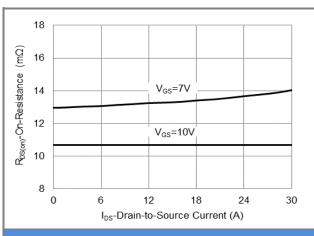


Fig.3 On-Resistance vs. Drain Current

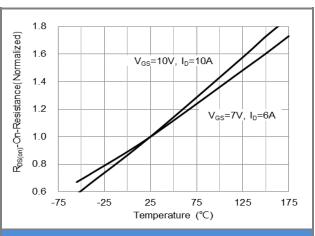


Fig.4 On-Resistance vs. Junction temperature

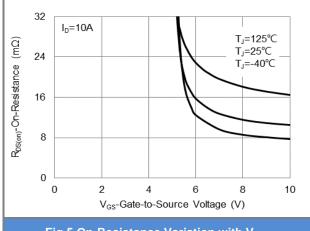
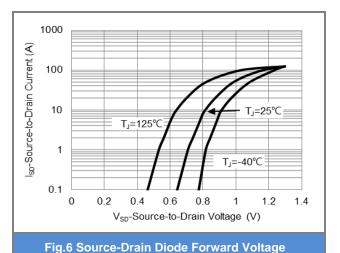


Fig.5 On-Resistance Variation with V_{GS}







TYPICAL CHARACTERISTIC CURVES

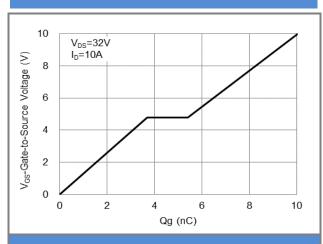


Fig.7 Gate-Charge Characteristics

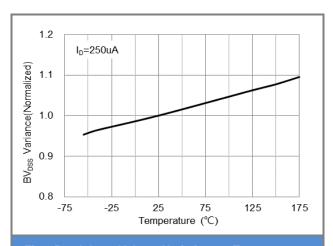


Fig.8 Breakdown Voltage Variation vs. Temperature

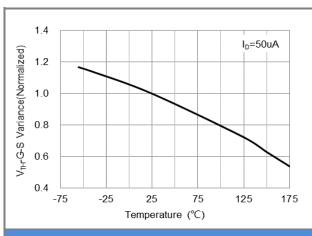


Fig.9 Threshold Voltage Variation with Temperature

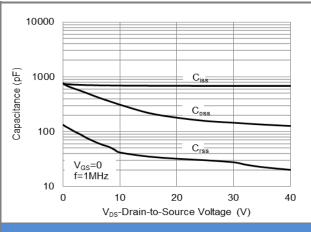
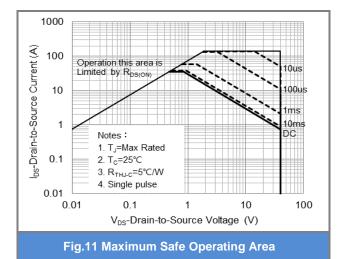


Fig.10 Capacitance vs. Drain-Source Voltage



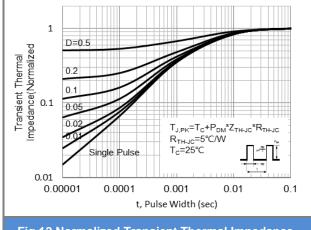


Fig.12 Normalized Transient Thermal Impedance

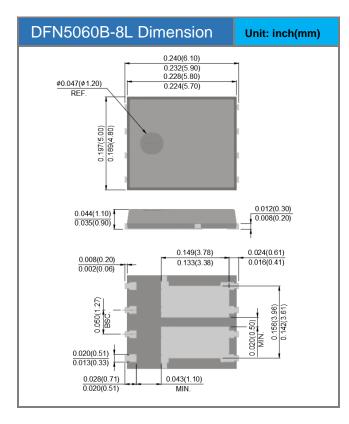


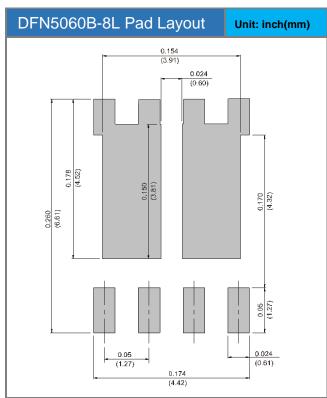


Product and Packing Information

Part No.	Package Type	Packing Type	Marking	
PJQ5948V-AU	DFN5060B-8L	3K pcs / 13" reel	Q5948V	

Packaging Information & Mounting Pad Layout









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